

FHX13LG, FHX14LG

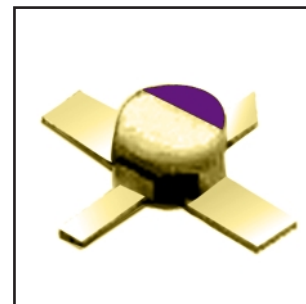
Super Low Noise HEMT

FEATURES

- Low Noise Figure: 0.45dB (Typ.)@f=12GHz (FHX13)
- High Associated Gain: 13.0dB (Typ.)@f=12GHz
- $L_g \leq 0.15\mu\text{m}$, $W_g = 200\mu\text{m}$
- Gold Gate Metallization for High Reliability
- Cost Effective Ceramic Microstrip (SMT) Package
- Tape and Reel Packaging Available

DESCRIPTION

The FHX13LG, FHX14LG is a Super High Electron Mobility Transistor(SuperHEMT™) intended for general purpose, ultra-low noise and high gain amplifiers in the 2-18GHz frequency range. The devices are packaged in cost effective, low parasitic, hermetically sealed metal-ceramic package for high volume telecommunication, TVRO, VSAT or other low noise applications.



Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature Ta=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	3.5	V
Gate-Source Voltage	V_{GS}	-3.0	V
Total Power Dissipation	P_t^*	180	mW
Storage Temperature	T_{stg}	-65 to +175	°C
Channel Temperature	T_{ch}	175	°C

*Note: Mounted on Al_2O_3 board (30 x 30 x 0.65mm)

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 2 volts.
2. The forward and reverse gate currents should not exceed 0.2 and -0.05 mA respectively with gate resistance of 4000Ω.
3. The operating channel temperature (T_{ch}) should not exceed 80°C.

ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta=25°C)

Item		Symbol	Condition	Limit			Unit
				Min.	Typ.	Max.	
Saturated Drain Current		I _{DSS}	V _{DS} = 2V, V _{GS} =0V	10	30	60	mA
Transconductance		g _m	V _{DS} = 2V, I _{DS} =10mA	35	50	-	mS
Pinch-off Voltage		V _p	V _{DS} = 2V, I _{DS} =1mA	-0.1	-0.7	-1.5	V
Gate Source Breakdown Voltage		V _{GSO}	I _{GS} = -10μA	-3.0	-	-	V
Noise Figure	FHX13LG	NF	V _{DS} = 2V, I _{DS} = 10mA, f = 12GHz	-	0.45	0.50	dB
Associated Gain		G _{as}		11.0	13.0	-	dB
Noise Figure	FHX14LG	NF		-	0.55	0.60	dB
Associated Gain		G _{as}		11.0	13.0	-	dB
Thermal Resistance		R _{th}	Channel to Case	-	300	400	°C/W

AVAILABLE CASE STYLES: LG

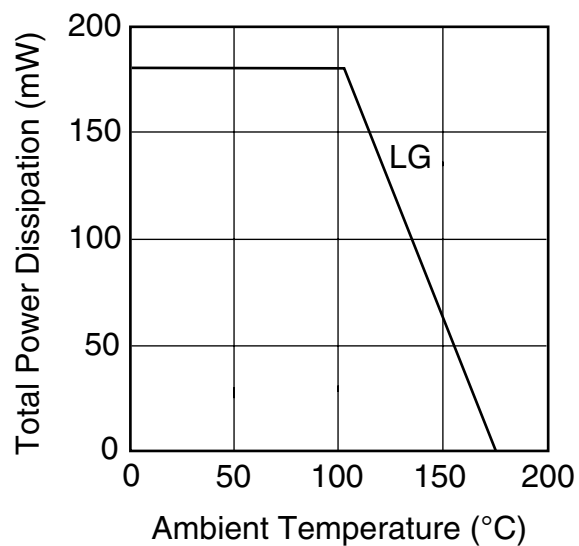
Note: RF parameters for LG devices are measured on a sample basis as follows:

Lot qty.			Sample qty.	Accept/Reject
1200	or	less	125	(0,1)
1201	to	3200	200	(0,1)
3201	to	10000	315	(1,2)
10001	or	over	500	(1,2)

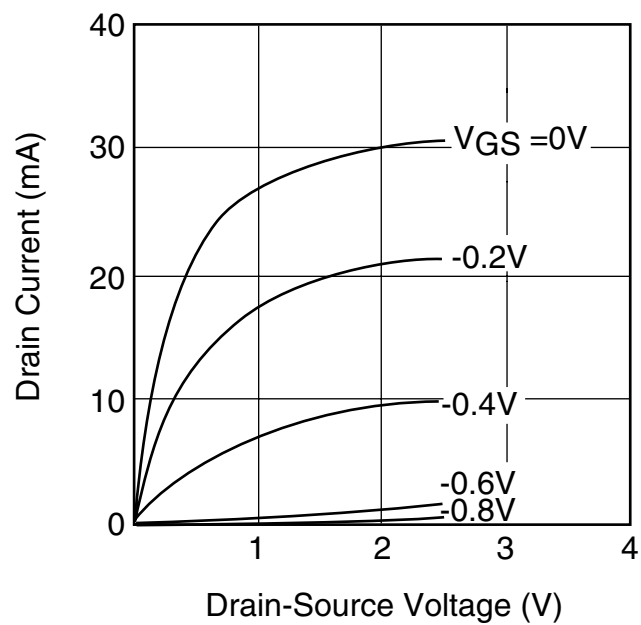
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POWER DERATING CURVE

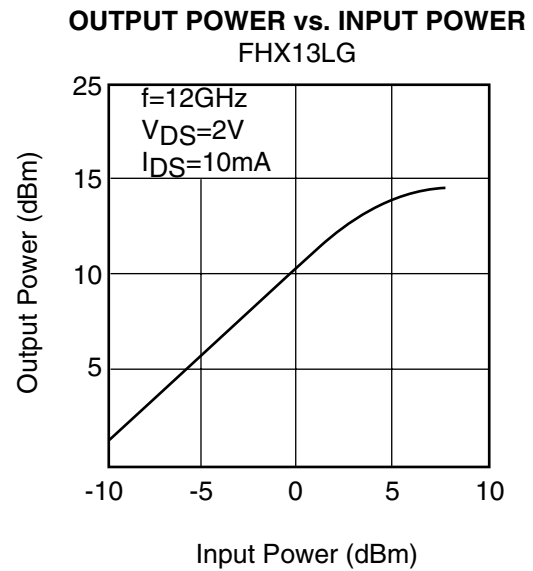
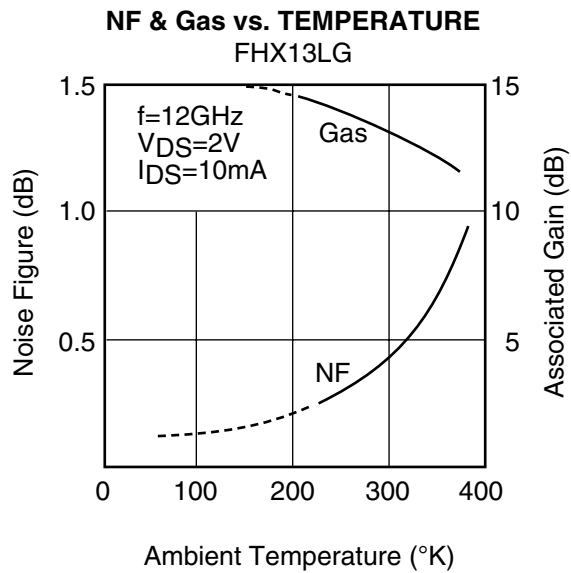
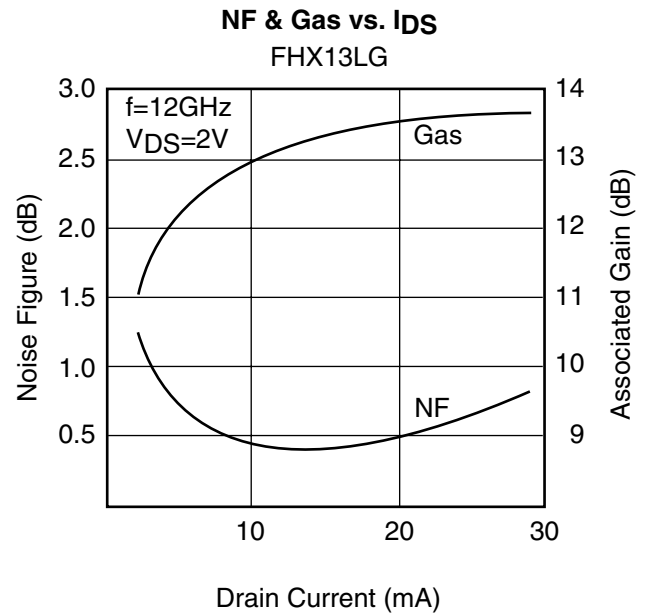
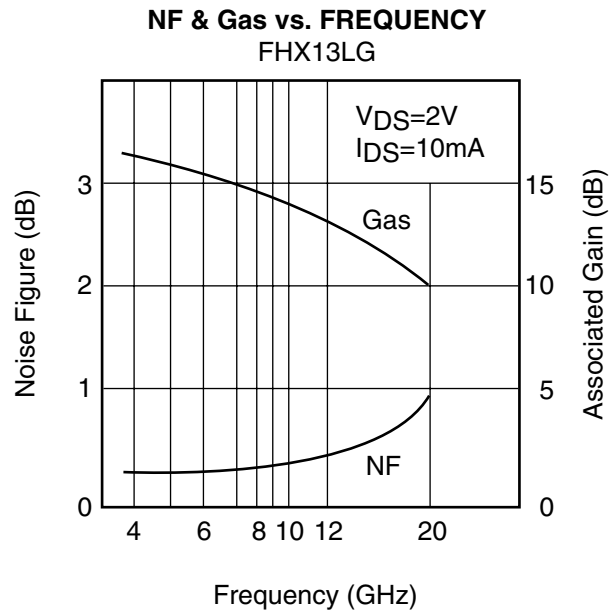


DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



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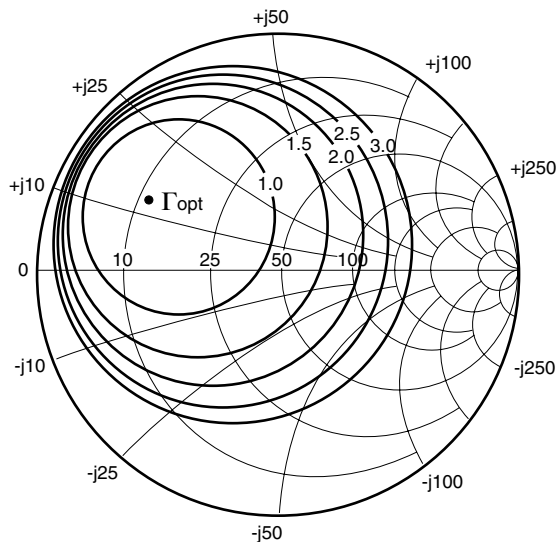


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TYPICAL NOISE FIGURE CIRCLE

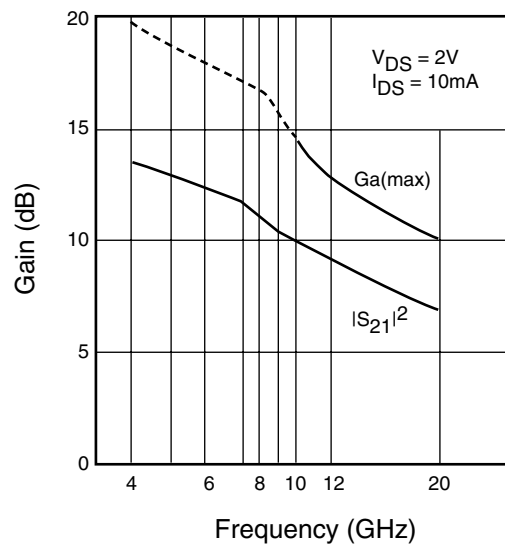
FHX13LG



f = 12 GHz
V_{DS} = 2V
I_{DS} = 10mA

Γ_{opt} = 0.61 ∠ 150°
R_n/50 = 0.04
NF_{min} = 0.45dB

Ga(max) & |S₂₁|² vs. FREQUENCY



NOISE PARAMETERS

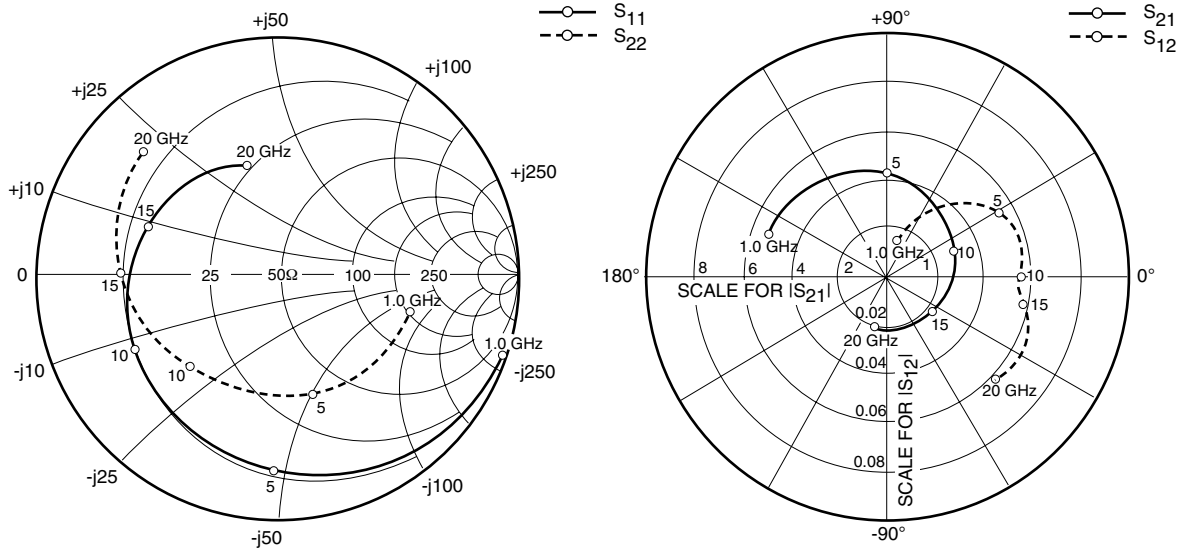
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V_{DS}=2V, I_{DS}=10mA

Freq. (GHz)	Γ _{opt} (MAG)	Γ _{opt} (ANG)	NF _{min} (dB)	R _n /50
2	0.96	29	0.33	0.22
4	0.92	57	0.34	0.20
6	0.86	83	0.35	0.15
8	0.79	107	0.37	0.11
10	0.71	129	0.40	0.07
12	0.61	150	0.45	0.04
14	0.50	168	0.53	0.04
16	0.38	-175	0.63	0.06
18	0.24	-161	0.83	0.10

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S-PARAMETERS

FHX13/14LG

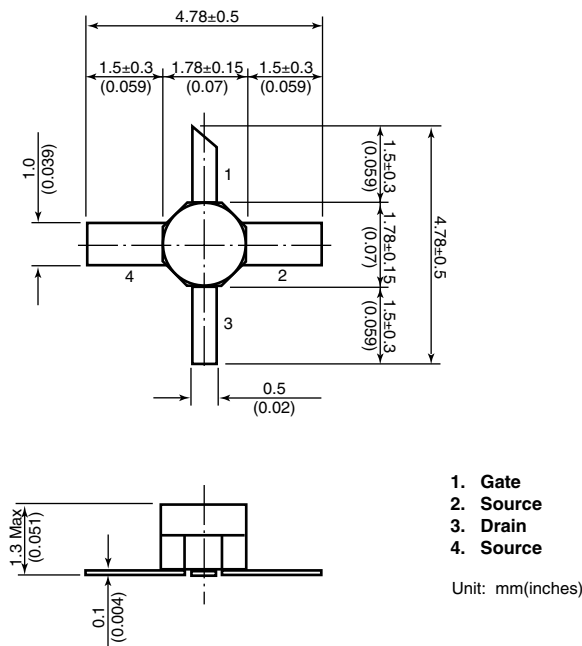
$V_{DS} = 2V$, $I_{DS} = 10mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1000	0.988	-20.0	5.327	160.1	0.015	75.7	0.574	-16.3
2000	0.956	-39.5	5.133	141.0	0.028	63.3	0.560	-32.1
3000	0.908	-58.1	4.851	123.0	0.039	50.1	0.539	-47.3
4000	0.862	-75.5	4.534	105.9	0.048	39.0	0.522	-62.0
5000	0.811	-91.6	4.213	89.7	0.053	29.3	0.502	-75.6
6000	0.763	-107.1	3.886	74.4	0.056	21.0	0.488	-89.6
7000	0.727	-121.1	3.582	60.0	0.057	13.2	0.487	-103.0
8000	0.701	-133.3	3.300	46.4	0.056	7.9	0.498	-114.9
9000	0.682	-144.1	3.078	33.8	0.055	3.5	0.515	-125.0
10000	0.659	-154.2	2.899	21.4	0.055	-0.0	0.531	-134.4
11000	0.636	-164.4	2.748	9.3	0.054	-2.6	0.544	-144.0
12000	0.618	-175.4	2.593	-3.3	0.054	-5.2	0.561	-155.1
13000	0.608	175.5	2.466	-14.8	0.054	-5.7	0.590	-164.0
14000	0.596	166.6	2.366	-26.6	0.055	-7.8	0.619	-172.4
15000	0.585	158.3	2.279	-38.3	0.056	-9.7	0.654	-179.7
16000	0.564	148.8	2.244	-50.7	0.058	-12.8	0.677	172.6
17000	0.543	138.2	2.217	-63.6	0.061	-17.6	0.701	163.4
18000	0.525	127.3	2.185	-77.1	0.063	-24.7	0.727	154.1
19000	0.506	116.2	2.143	-91.4	0.063	-33.1	0.748	143.6
20000	0.470	106.5	2.089	-105.4	0.061	-43.7	0.763	137.2

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Case Style "LG" Metal-Ceramic Hermetic Package



For further information please contact:

FUJITSU COMPOUND SEMICONDUCTOR, INC.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
Phone: (408) 232-9500
FAX: (408) 428-9111
www.fcsi.fujitsu.com

FUJITSU MICROELECTRONICS, LTD.

Compound Semiconductor Division
Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
Phone: +44 (0)1628 504800
FAX: +44 (0)1628 504888

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